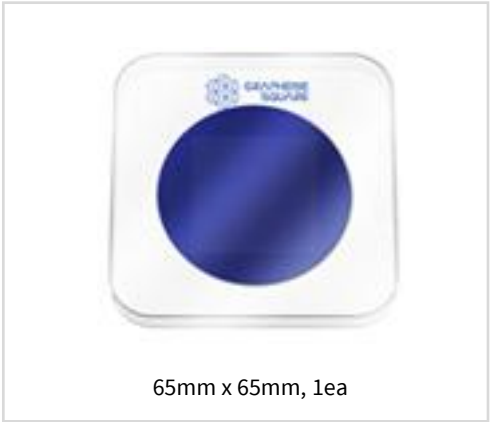




CVD Graphene on Cu foil

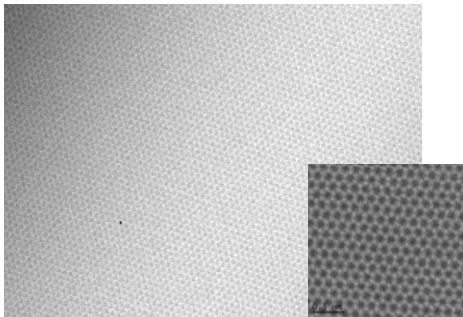
Ultra-Clean Graphene on SiO₂/Si Wafer



65mm x 65mm, 1ea

| | |
|------------------|---|
| Product Size | Up to 90 x 90 mm ² (Max) |
| Film Morphology | Continuous Monolayer (>95%) |
| Sheet Resistance | Av. < 250~400 Ω/sq |
| Mobility | >3500 cm ² /Vs (Max. 17,000 cm ² /Vs) |
| Transmittance | >97% |
| Substrate | SiO ₂ (300nm)/Si wafer (Standard) |
| Domain Size | 10-20 μm |

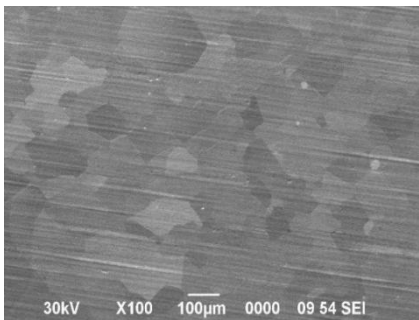
High-Resolution TEM Images



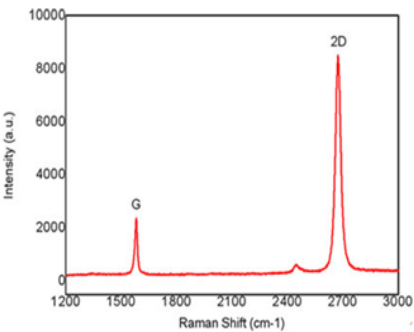
Substrate specifications

| | |
|-----------------|-------------|
| Orientation | <100> |
| Thickness | 525±25 μm |
| Oxide Thickness | 300nm |
| Type/Dopant | P/Boron |
| Resistivity | Resistivity |

SEM Image of Graphene on Cu

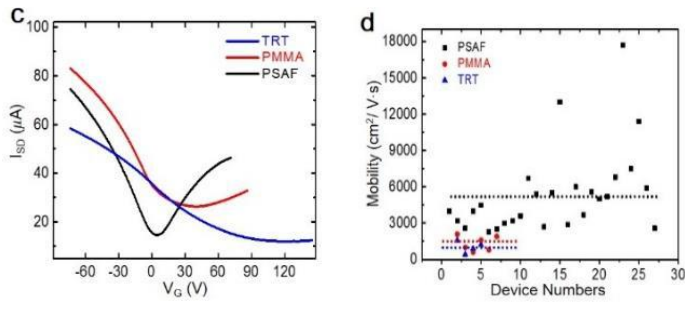


Raman Spectrum

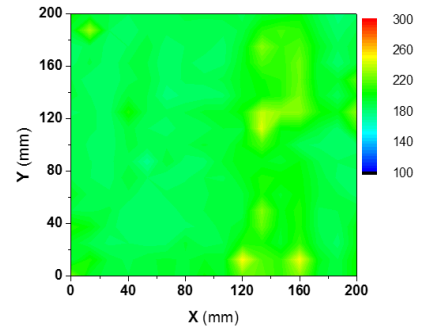




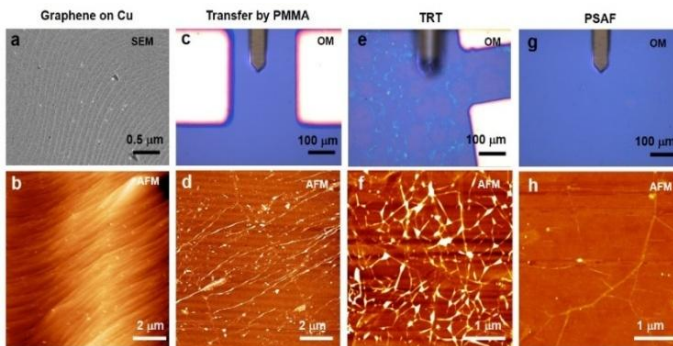
Electrical Properties



Sheet Resistance Uniformity



Ultra-Clean Transfer by Pressure Sensitive Adhesive Films



Reference

- (1) S. Kim *et al.* Ultra-Clean Patterned Transfer of Single-Layer Graphene by Recyclable Pressure Sensitive Adhesive Films. *Nano Lett.* (accepted).
- (2) S. Bae*, H. Kim* *et al.* Roll-to-roll production of 30 inch graphene films for transparent electrodes *Nature Nanotech.* **5**, 574 (2010).